



**DMTH6005LK3** 

#### 60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	Ι <sub>D</sub> T <sub>C</sub> = +25°C
60V	5.6mΩ @ V <sub>GS</sub> = 10V	90A

## **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- **Engine Management Systems**
- **Body Control Electronics**
- **DCDC** Converters

#### **Features**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching ensures more reliable and robust end application
- Low R<sub>DS(ON)</sub> minimizes power losses
- Low Q<sub>a</sub> minimizes switching losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

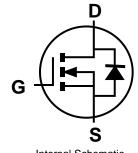
### **Mechanical Data**

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)



Ш D G Top View Pin Out

D



Internal Schematic

### Ordering Information (Note 4)

	Part Number	Case	Packaging		
	DMTH6005LK3-13	TO252	2,500/Tape & Reel		
Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.					

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



**D**II = Manufacturer's Marking H6005L = Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 15 = 2015)WW = Week Code (01 to 53)



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V <sub>DSS</sub>	60	V		
Gate-Source Voltage	V <sub>GSS</sub>	±20	V		
Continuous Drain Current (Note 6)	T <sub>C</sub> = +25°C (Note 9)	ID	90	А	
	$T_{C} = +100^{\circ}C$		70		
Maximum Body Diode Forward Current (Note 6)	T <sub>C</sub> = +25°C	Is	90	A	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	150	A		
Avalanche Current, L=1mH	I <sub>AS</sub>	14.8	A		
Avalanche Energy, L=1mH	E <sub>AS</sub>	98	mJ		

### **Thermal Characteristics**

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	2.1	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{ heta JA}$	38	°C/W
Total Power Dissipation (Note 6)	PD	100	W	
Thermal Resistance, Junction to Case (Note 6)		R <sub>0JC</sub>	1.5	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +175	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	<b>.</b>		- 71-				
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60			V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)						·	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	_	3	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
		_	4.5	5.6		$V_{GS} = 10V, I_D = 50A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	5.6	7.2	mΩ	$V_{GS} = 6V, I_D = 20A$	
		_	7.9	10		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 12.5A	
Diode Forward Voltage	V <sub>SD</sub>	_	_	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	_	2962	_			
Output Capacitance	Coss		965.2	—	pF	$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	Crss	_	59.8	_			
Gate Resistance	R <sub>G</sub>	_	0.66	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	47.1	—			
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	23.1	_	nC	N/ 201/ 1 50A	
Gate-Source Charge	Q <sub>gs</sub>		10.2		nc	$V_{DD} = 30V, I_D = 50A$	
Gate-Drain Charge	Q <sub>gd</sub>	_	12.5	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	8.3	_			
Turn-On Rise Time	t <sub>R</sub>	_	9.4	_		$V_{DD} = 30V, V_{GS} = 10V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>		22	_	ns	$I_D = 30A, R_G = 3.3\Omega$	
Turn-Off Fall Time	tF		8.9	_	]		
Body Diode Reverse Recovery Time	t <sub>RR</sub>		40.4	_	ns		
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>		49.7	_	nC	-I <sub>F</sub> = 30A, di/dt = 100A/μs	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout. Notes:

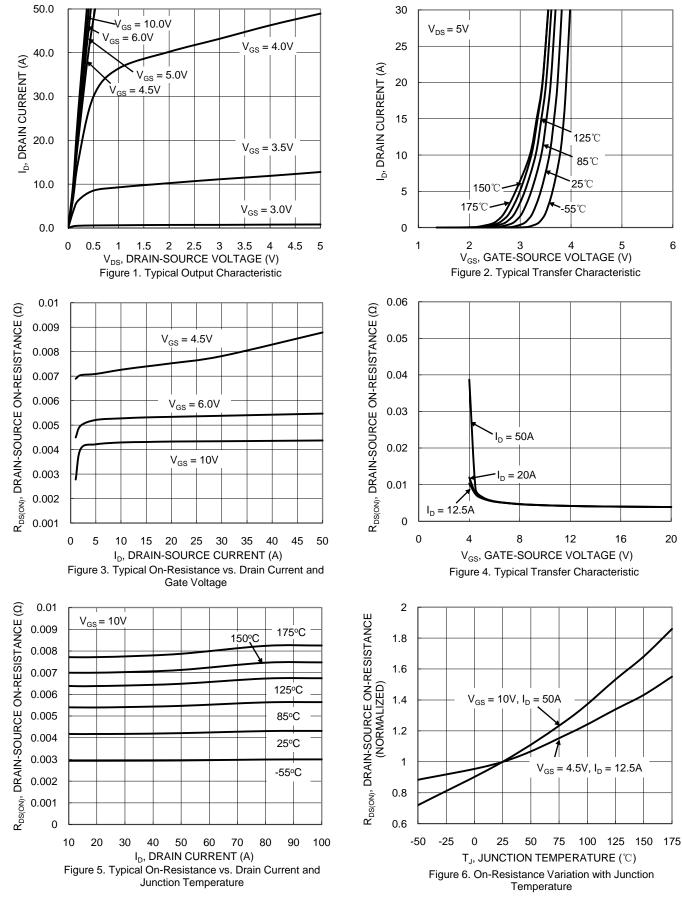
Thermal resistance from junction to soldering point (on the exposed drain pad).
Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to production testing.

9. Package limited.



### DMTH6005LK3

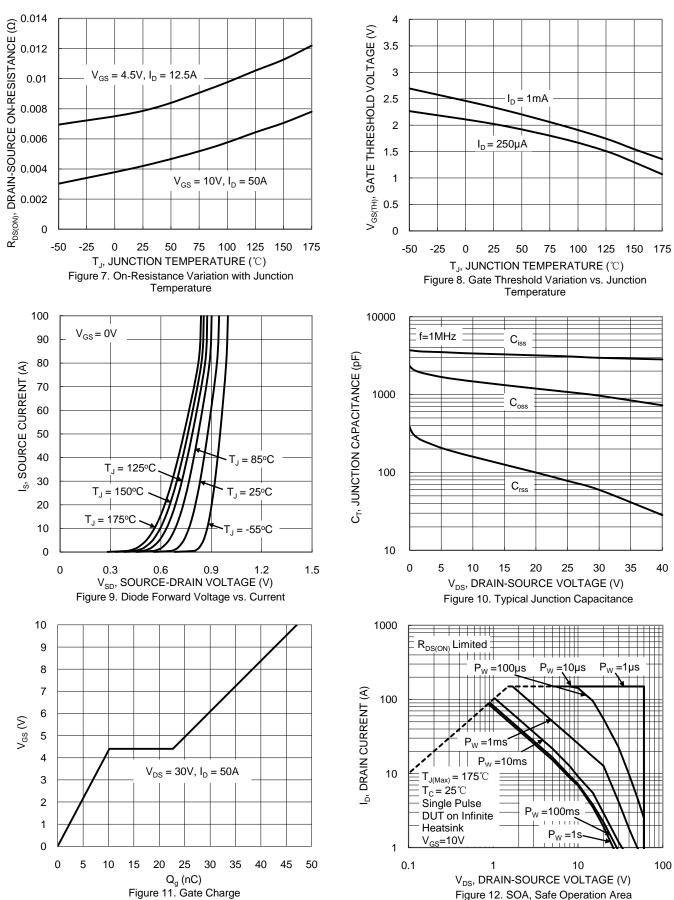


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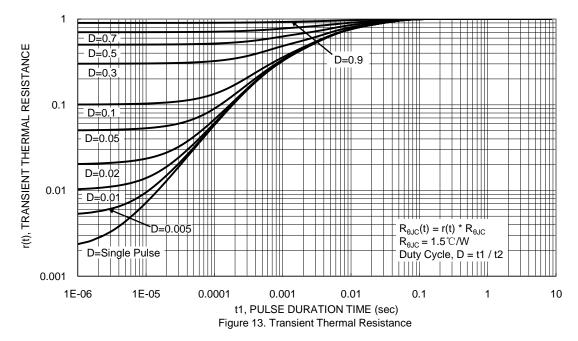




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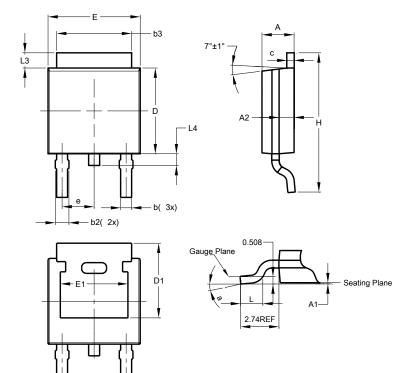




# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

#### TO252 (DPAK)

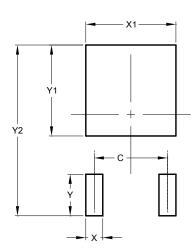


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39 2.29			
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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